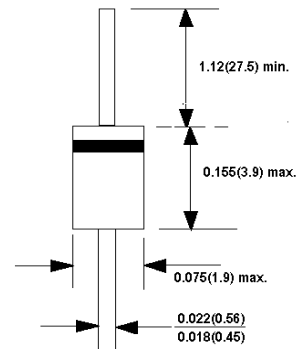
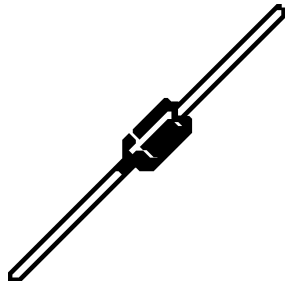


Description

Mechanical Dimensions

1N4148/1N4448



DO-35 (Glass)

Dimensions in inches(mm)

Features

- Silicon Epitaxial Planar Diode
- 500mW Power Dissipation
- Pb Free product are Available
- Bulk--2K, 13" T/R--10K, T/B--5K Ammo Box

Mechanical Data

- Case: DO-35 Glass
- Terminals: Solderable per MIL-STD-202E Method 208
- Polarity: Cathode Band
- Weight: 0.13grams

Max Ratings at Tj=25C Unless Otherwise Specified

Characteristic	Syb	1N4148 / 1N4448	Unit
Reverse Voltage	Vr	75	V
Peak Reverse Voltage	VRM	100	V
Average Rectified Current	IF(AV)	150	mA
Surge Forward Current at t<1s	IFSM	500	mA
Power Dissipation Derate above at 25C	Pd	500	mW
Storage Temp. Range	Ts	-55 ~ +200	C
Junction Temp. Range	Tj	200	C
Max Forward Voltage @ If=10mA ---1N4148 If=100mA--1N4448	VF	1.0 max	V
Reverse Voltage Leakage Current Vr=20V Vr=75V Vr=25V at Tj=150C	Ir	25 5 50	uA
Reerse Breakdown Voltage tested width 100uA	Vbr	100 min.	V
Voltage rise when switching on tseted with 50mA pulses tp=0.1us, rise time<30ns, fp=5~100kHz	Vfr	2.5 max.	V
Recerse Recovery Time	trr	4 max.	nS
Capacitance at VF=VR=0	Ctot	4	pF
Max Thermal Resistance Junction to Ambient Air	Rthja	350	k / W

* lead lept at ambient temp. at 8mm length

Typical Characteristics ($T_{amb} = 25^\circ\text{C}$ unless otherwise specified)

Figure 1. Forward Characteristics

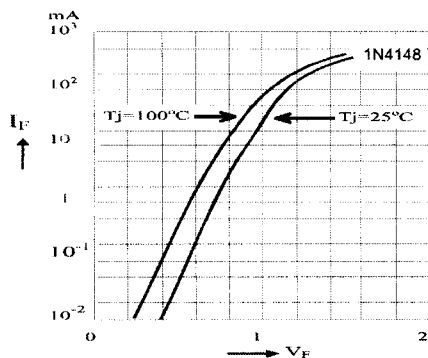
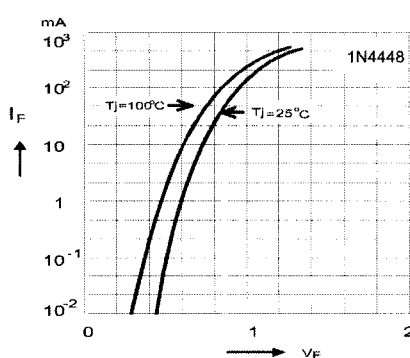
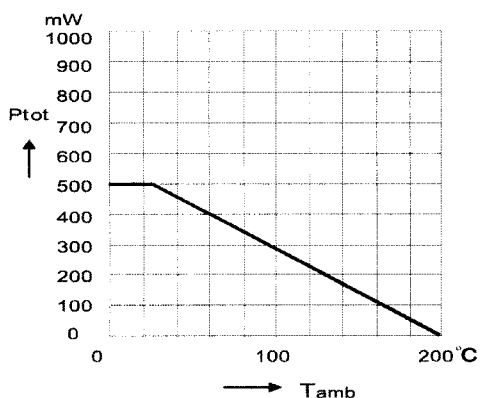


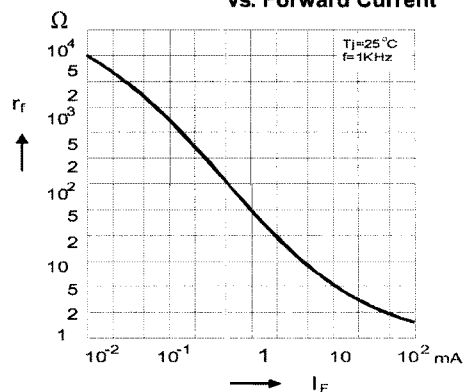
Figure 2. Forward Characteristics



**Figure 3. Admissible Power Dissipation
vs. Ambient Temperature**



**Figure 4. Dynamic Forward Resistance
vs. Forward Current**



**Figure 5. Relative Capacitance vs.
Reverse Voltage**

